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FAX

Date: June 3, 2004 **Pages (including cover):**

To: Examiner Brewster - USPTO **Fax:** 571-272-1854 **Ph:** 571-272-1854

From: Donald R. Studebaker

Message: U.S. Patent Application No. 09/662,004
Our Reference: 740819-418

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Docket No. 740819-418

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:)
Kazuichiro ITONAGA et al.) Group Art Unit: 2823
Serial No. 09/662,004) Examiner: William M. Brewster
Filed: September 14, 2000) Confirmation No. 9057
For: METHOD OF FORMING INSULATING) Date: June 3, 2004
FILM AND METHOD OF
FABRICATING SEMICONDUCTOR
DEVICE

AMENDMENT PURSUANT TO 37 C.F.R. §1.312

Mail Stop **Issue Fee**
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Prior to issuance, please amend the above-identified application identified in caption as follows:

IN THE CLAIMS:

1. (Previously Presented) A method of forming an insulating film on a semiconductor layer, comprising the steps of:

(a) loading a substrate including said semiconductor layer on a lower electrode in a processing chamber; and

(b) generating, within the processing chamber, plasma biased toward said substrate by introducing only oxygen into the processing chamber and with the substrate heated to a temperature of up to 300°C, thereafter subjecting said semiconductor layer to the biased plasma,

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